

Title (en)

COMPOSITIONS AND METHODS USING SAME FOR THERMAL DEPOSITION SILICON-CONTAINING FILMS

Title (de)

ZUSAMMENSETZUNGEN UND VERFAHREN DAMIT ZUR THERMISCHEN ABSCHIEDUNG VON SILICIUMHALTIGEN FILMEN

Title (fr)

COMPOSITIONS ET PROCÉDÉS FAISANT APPEL À CELLES-CI POUR LE DÉPÔT THERMIQUE DE FILMS CONTENANT DU SILICIUM

Publication

EP 3963122 A1 20220309 (EN)

Application

EP 20809007 A 20200521

Priority

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- US 2020033897 W 20200521

Abstract (en)

[origin: WO2020236994A1] A composition is used in a process for depositing a silicon oxide film or a carbon doped silicon oxide film using a deposition process, wherein the composition includes at least one silicon precursor having a structure represented by Formula I as described herein.

IPC 8 full level

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CPC (source: CN EP KR US)

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